ON5088 NPN wideband silicon germanium RF transistor

Rev. 3 — 12 December 2012

Product data sheet

1. Product profile

1.1 General description

NPN silicon germanium microwave transistor for high speed, low noise applications in a plastic, 4-pin dual-emitter SOT343F package.

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

1.2 Features and benefits

- Low noise high gain microwave transistor
- High maximum stable gain 27 dB at 1.8 GHz
- 110 GHz f_T silicon germanium technology

1.3 Applications

- 2nd and 3rd LNA stage in DBS LNBs
- Satellite radio
- Low noise amplifiers for microwave communications systems
- WLAN and WiMAX applications
- Analog/digital cordless applications

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Ν	/lin	Тур	Max	Unit
V _{CB}	collector-base voltage	open emitter	-		-	10	V
V_{CE}	collector-emitter voltage	open base	-		-	3.0	V
		shorted base	-		-	10	V
V_{EB}	emitter-base voltage	open collector	-		-	1.0	V
I _C	collector current		-		25	40	mA
P _{tot}	total power dissipation	$T_{sp} \le 90 \ ^{\circ}C$	<u>[1]</u> -		-	136	mW
h _{FE}	DC current gain	$ I_C = 10 \text{ mA}; \text{V}_{CE} = 2 \text{ V}; $	1	60	280	400	
C_{CBS}	collector-base capacitance	$V_{CB} = 2 V$; f = 1 MHz	-		70	-	fF



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Table 1.	Quick reference data	commueu				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _T	transition frequency	$I_{C} = 25 \text{ mA}; V_{CE} = 2 \text{ V};$ f = 2 GHz; T _{amb} = 25 °C	-	55	-	GHz
G _{p(max)}	maximum power gain	$I_{C} = 25 \text{ mA}; V_{CE} = 2 \text{ V};$ f = 12 GHz; T _{amb} = 25 °C	[2] _	13	-	dB
NF	noise figure	$\begin{split} I_{C} &= 5 \text{ mA; } V_{CE} = 2 \text{ V;} \\ f &= 12 \text{ GHz; } \Gamma_{S} = \Gamma_{opt}; \\ T_{amb} &= 25 ^{\circ}\text{C} \end{split}$	-	1.1	-	dB

 Table 1.
 Quick reference data ...continued

[1] T_{sp} is the temperature at the solder point of the emitter lead.

[2] $G_{p(max)}$ is the maximum power gain, if K > 1. If K < 1 then $G_{p(max)}$ = Maximum Stable Gain (MSG).

2. Pinning information

Table 2.	Discrete pinning		
Pin	Description	Simplified outline	Graphic symbol
1	emitter		
2	base		4
3	emitter		2
4	collector		1
			1, 3
		2 1	mbb159

3. Ordering information

Table 3. Order	ring informa	tion	
Type number	Package		
	Name	Description	Version
ON5088	-	plastic surface-mounted flat pack package; reverse pinning; 4 leads	SOT343F

4. Marking

Marking	Description
*6N	* = p : made in Hong Kong
	* = t : made in Malaysia
	* = W : made in China
	J

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5. Limiting values

Table 5. In accorda	Limiting values nce with the Absolute Maximu	ım Rating System ((IEC 60134).		
Symbol	Parameter	Conditions	Min	Max	Unit
V _{CB}	collector-base voltage	open emitter	-	10	V
V _{CE}	collector-emitter voltage	open base	-	3.0	V
		shorted base	-	10	V
V_{EB}	emitter-base voltage	open collector	-	1.0	V
I _C	collector current		-	40	mA
P _{tot}	total power dissipation	$T_{sp} \le 90 \ ^{\circ}C$	<u>[1]</u> _	136	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C

[1] T_{sp} is the temperature at the solder point of the emitter lead.

Thermal characteristics 6.

Table 6.	Thermal characteristics			
Symbol	Parameter	Conditions	Тур	Unit
R _{th(j-sp)}	thermal resistance from junction to solder point		440	K/W

Characteristics 7.

Table 7.	Characteristics
T _ 25 °C	unloss otherwise a

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{(BR)CBO}	collector-base breakdown voltage	$I_{C} = 2.5 \ \mu A; I_{E} = 0 \ mA$	10	-	-	V
V _{(BR)CEO}	collector-emitter breakdown voltage	$I_C = 1 \text{ mA}; I_B = 0 \text{ mA}$	3.0	-	-	V
I _C	collector current		-	25	40	mA
I _{CBO}	collector-base cut-off current	I _E = 0 mA; V _{CB} = 4.5 V	-	-	100	nA
h _{FE}	DC current gain	I_{C} = 10 mA; V_{CE} = 2 V	160	280	400	
C _{CES}	collector-emitter capacitance	V _{CB} = 2 V; f = 1 MHz	-	268	-	fF
C _{EBS}	emitter-base capacitance	V _{EB} = 0.5 V; f = 1 MHz	-	400	-	fF
C _{CBS}	collector-base capacitance	V _{CB} = 2 V; f = 1 MHz	-	70	-	fF
f _T	transition frequency	I_{C} = 25 mA; V_{CE} = 2 V; f = 2 GHz; T_{amb} = 25 °C	-	55	-	GHz
G _{p(max)}	maximum power gain	I_C = 25 mA; V_{CE} = 2 V; T_{amb} = 25 °C	[1]			
		f = 1.8 GHz	-	27	-	dB
		f = 12 GHz	-	13	-	dB
$ s_{21} ^2$	insertion power gain	I_{C} = 25 mA; V_{CE} = 2 V; T_{amb} = 25 °C				
		f = 1.8 GHz	-	25.4	-	dB
		f = 12 GHz	-	9.3	-	dB

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Table 7.	Characteristics	continued
$T_i = 25 \ ^{\circ}C$	unless otherwise s	specified.

, uniess ourierwise specified.					
Parameter	Conditions	Min	Тур	Max	Unit
noise figure	$I_C = 5 \text{ mA}; V_{CE} = 2 \text{ V}; \Gamma_S = \Gamma_{opt}; T_{amb} = 25 \text{ °C}$				
	f = 1.8 GHz	-	0.43	-	dB
	f = 12 GHz	-	1.1	-	dB
associated gain	$I_C = 5 \text{ mA}; V_{CE} = 2 \text{ V}; \Gamma_S = \Gamma_{opt}; T_{amb} = 25 \text{ °C}$				
	f = 1.8 GHz	-	22	-	dB
	f = 12 GHz	-	10	-	dB
output power at 1 dB gain compression	$\rm I_C$ = 25 mA; $\rm V_{CE}$ = 2 V; $\rm Z_S$ = $\rm Z_L$ = 50 $\Omega;$ $\rm T_{amb}$ = 25 °C; f = 1.8 GHz	-	9	-	dBm
third-order intercept point	I _C = 25 mA; V _{CE} = 2 V; Z _S = Z _L = 50 Ω; T _{amb} = 25 °C; f ₂ = f ₁ + 1 MHz; f ₁ = 1.8 GHz	-	17	-	dBm
	Parameter noise figure associated gain output power at 1 dB gain compression	$\begin{array}{c} \mbox{Parameter} & \mbox{Conditions} \\ \mbox{noise figure} & I_C = 5 \mbox{ mA}; \mbox{ $V_{CE} = 2$ V; $\Gamma_S = Γ_{opt}; $T_{amb} = 25$ °C \\ \hline f = 1.8 \mbox{ GHz} \\ \hline f = 12 \mbox{ GHz} \\ \mbox{associated gain} & I_C = 5 \mbox{ mA}; \mbox{ $V_{CE} = 2$ V; $\Gamma_S = Γ_{opt}; $T_{amb} = 25$ °C \\ \hline f = 1.8 \mbox{ GHz} \\ \hline f = 12 \mbox{ GHz} \\ \hline f = 12 \mbox{ GHz} \\ \mbox{f} = 12 \mbox{ GHz} \\ \mbox{f} = 12 \mbox{ GHz} \\ \mbox{f} = 1.8 \mbox{ GHz} \\ \mbox{f} = 2 \mbox{V}; \mbox{Z}_S = \mbox{Z}_L = 50 \mbox{ Ω; $T_{amb} = 25$ °C;} \\ \mbox{f} = 1.8 \mbox{ GHz} \\ \mbox{f} = 1.8 \mbox{ GHz} \\ \mbox{f} = 1.8 \mbox{GHz} \\ \mbox{GHz} \\ \mbox{f} = 2 \mbox{V}; \mbox{GHz} \\ $	$\begin{tabular}{ c c c } \hline Parameter & Conditions & Min \\ noise figure & $I_C = 5 \mbox{ mA}; \mbox{ $V_{CE} = 2 \mbox{ V}; \mbox{ $\Gamma_S = \mbox{ Γ_{opt}; $T_{amb} = 25 \mbox{ \circC$}$} \\ \hline f = 1.8 \mbox{ GHz} & -$$$$$$$$$$$$$$$$$$$$$$$$$$$$$$$$$$$	$\begin{array}{c c c c c c } \mbox{Parameter} & \mbox{Conditions} & \mbox{Min} & \mbox{Typ} \\ \hline \mbox{noise figure} & & I_C = 5 \mbox{ mA}; \ V_{CE} = 2 \ V; \ \Gamma_S = \ \Gamma_{opt}; \ T_{amb} = 25 \ ^{\circ}C & & & & & & & & & & & & & & & & & & &$	$\begin{tabular}{ c c c } \hline Parameter & Conditions & Ic & Sm(1) & Typ & Max \\ \hline noise figure & I_C = 5 mA; \ V_{CE} = 2 \ V; \ \Gamma_S = \ \Gamma_{opt}; \ T_{amb} = 25 \ ^{\circ}C & & & & & & & & & & & & & & & & & & &$

 $\label{eq:general} \mbox{[1]} \quad G_{p(max)} \mbox{ is the maximum power gain, if } K > 1. \mbox{ If } K < 1 \mbox{ then } G_{p(max)} = MSG.$

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8. Package outline

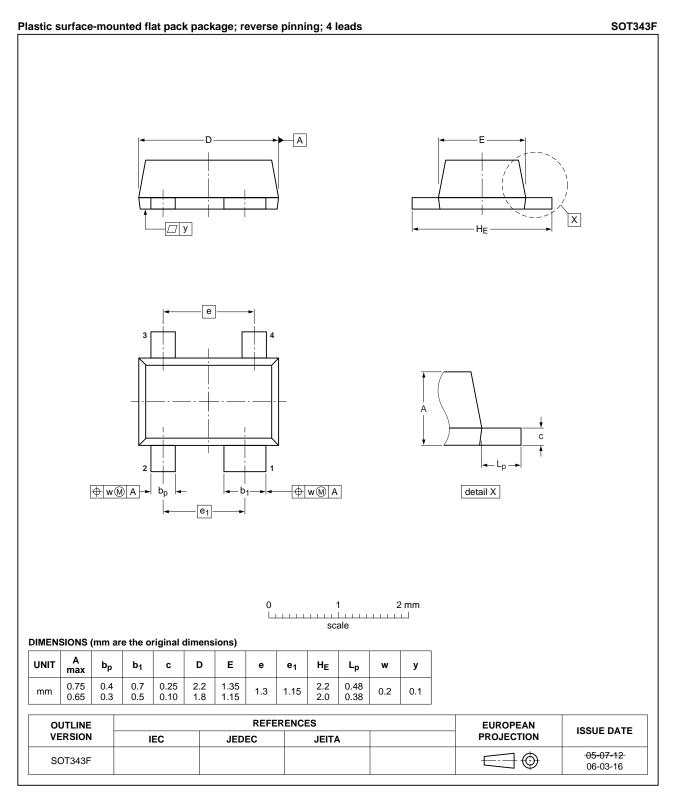


Fig 1. Package outline SOT343F

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9. Abbreviations

Table 8.	Abbreviations		
Acronym	Description		
DBS	Direct Broadcast Satellite		
DC	Direct Current		
DRO	Dielectric Resonator Oscillator		
LNA	Low Noise Amplifier		
LNB	Low Noise Block		
NPN	Negative-Positive-Negative		
RF	Radio Frequency		
WLAN	Wireless Local Area Network		
WiMAX	Worldwide Interoperability for Microwave Access		

10. Revision history

Table 9. Revision	history			
Document ID	Release date	Data sheet status	Change notice	Supersedes
ON5088 v.3	20121212	Product data sheet	-	ON5088 v.2
Modifications:	• Table 5 on p	b <mark>age 1</mark> : some changes hav b <mark>age 3</mark> : some changes hav	e been made.	
	 Table 7 on p 	age 3: The minimum value	e for V _{(BR)CEO} has been o	changed.
ON5088 v.2	20111222	Product data sheet	-	ON5088 v.1
ON5088 v.1	20100422	Product data sheet	-	-

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11.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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[2] The term 'short data sheet' is explained in section "Definitions".

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